# 30V P-CHANNEL ENHANCEMENT MODE MOSFET

**SUMMARY** 

 $V_{(BR)DSS} = -30V$ ;  $R_{DS(ON)} = 0.040\Omega$ ;  $I_D = -6.7A$ 

## **DESCRIPTION**

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.



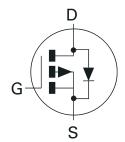
**SO8** 

## **FEATURES**

- Low on-resistance
- · Fast switching speed
- · Low threshold
- · Low gate drive
- Low profile SOIC package

## **APPLICATIONS**

- Disconnect switches
- Motor control



## **ORDERING INFORMATION**

DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP3A16N8TA	7″	12mm	500 units
ZXMP3A16N8TC	13"	12mm	2500 units

## **DEVICE MARKING**

 ZXMP 3A16

## **PINOUT**



Top View



## **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	-30	V
Gate Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current $V_{GS}$ =-10V; $T_A$ =25°C (b) $V_{GS}$ =-10V; $T_A$ =70°C (b) $V_{GS}$ =-10V; $T_A$ =25°C (a)	I <sub>D</sub>	-6.7 -5.4 -5.6	А
Pulsed Drain Current (c)	I <sub>DM</sub>	-26	А
Continuous Source Current (Body Diode) (b)	I <sub>S</sub>	-3.2	А
Pulsed Source Current (Body Diode) (c)	I <sub>SM</sub>	-26	А
Power Dissipation at T <sub>A</sub> =25°C (a) Linear Derating Factor	P <sub>D</sub>	1.9 15.2	W mW/°C
Power Dissipation at T <sub>A</sub> =25°C (b) Linear Derating Factor	P <sub>D</sub>	2.8 22.4	W mW/°C
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

## THERMAL RESISTANCE

PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	65	°C/W
Junction to Ambient (b)	$R_{\theta JA}$	45	°C/W

### NOTES

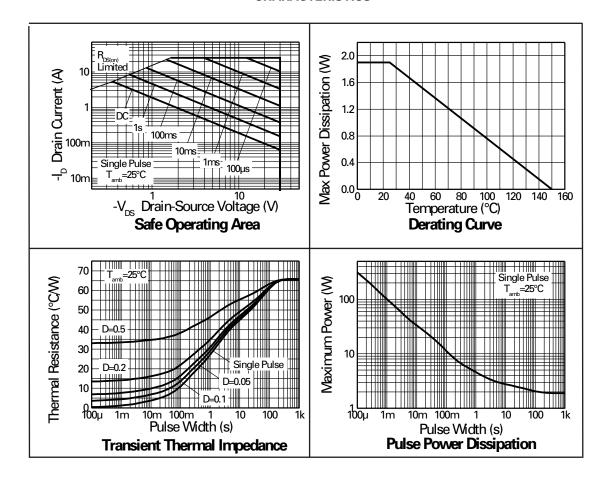
 $(a) For a device surface mounted on 25 mm \times 25 mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions and the surface of the s$ 



<sup>(</sup>b) For a device surface mounted on FR4 PCB measured at t≤5 secs.

<sup>(</sup>c) Repetitive rating 25mm x 25mm FR4 PCB, D = 0.05, pulse width  $10\mu s$  - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

## **CHARACTERISTICS**





# **ELECTRICAL CHARACTERISTICS** (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

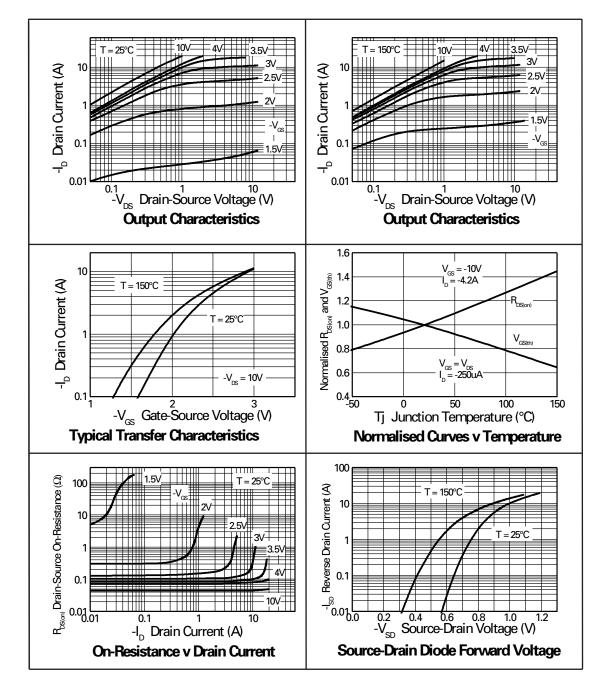
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	
STATIC		•				•	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	-30			V	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1.0	μΑ	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	
Gate-Body Leakage	I <sub>GSS</sub>			100	nA	$V_{GS}$ = $\pm 20V$ , $V_{DS}$ = $0V$	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	-1.0			V	$I_D = -250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-State Resistance (1)	R <sub>DS(on)</sub>			0.040 0.070	$\Omega \Omega$	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3.4A	
Forward Transconductance (1)(3)	g <sub>fs</sub>		9.2		S	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4.2A	
DYNAMIC (3)		'	•	•			
Input Capacitance	C <sub>iss</sub>		1022		pF		
Output Capacitance	Coss		267		pF	V <sub>DS</sub> =-15 V, V <sub>GS</sub> =0V, f=1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		229		pF		
SWITCHING(2) (3)							
Turn-On Delay Time	t <sub>d(on)</sub>		3.8		ns	V <sub>DD</sub> =-15V, I <sub>D</sub> =-1A	
Rise Time	t <sub>r</sub>		6.5		ns		
Turn-Off Delay Time	t <sub>d(off)</sub>		37.1		ns	$R_G=6.0\Omega$ , $V_{GS}=-10V$	
Fall Time	t <sub>f</sub>		21.4		ns		
Gate Charge	$Q_g$		17.2		nC	V <sub>DS</sub> =-15V,V <sub>GS</sub> =-5V, I <sub>D</sub> =-4.2A	
Total Gate Charge	Qg		29.6		nC	V <sub>DS</sub> =-15V,V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A	
Gate-Source Charge	Q <sub>gs</sub>		2.8		nC		
Gate-Drain Charge	Q <sub>gd</sub>		8.6		nC		
SOURCE-DRAIN DIODE						,	
Diode Forward Voltage (1)	V <sub>SD</sub>		-0.85	-0.95	V	T <sub>J</sub> =25°C, I <sub>S</sub> =-3.6A, V <sub>GS</sub> =0V	
Reverse Recovery Time (3)	t <sub>rr</sub>		21.7		ns	T <sub>J</sub> =25°C, I <sub>F</sub> =-2A, di/dt= 100A/μs	
Reverse Recovery Charge (3)	Q <sub>rr</sub>		16.1		nC		

### NOTES

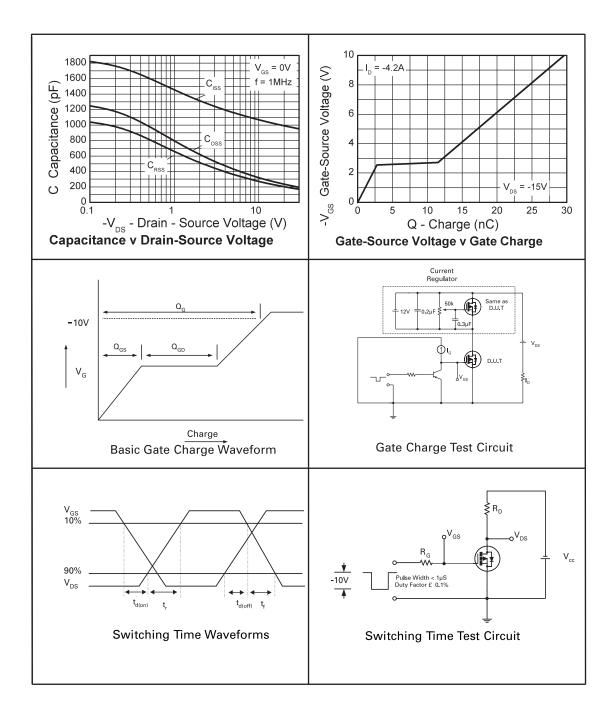
- (1) Measured under pulsed conditions. Width  ${\leq}300\mu s.$  Duty cycle  ${\leq}\,2\%$  .
- (2) Switching characteristics are independent of operating junction temperature.
- (3) For design aid only, not subject to production testing.



## **CHARACTERISTICS**









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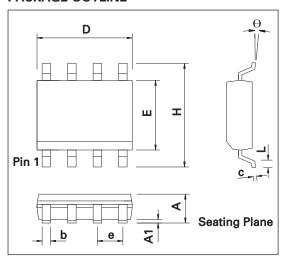
- "Preview"Future device intended for production at some point. Samples may be available
- "Active"Product status recommended for new designs
- "Last time buy (LTB)"Device will be discontinued and last time buy period and delivery is in effect
- "Not recommended for new designs"Device is still in production to support existing designs and production
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## **PACKAGE OUTLINE**



CONTROLLING DIMENSIONS ARE IN INCHES APPROX IN MILLIMETERS

## **PACKAGE DIMENSIONS**

DIM	Millin	neters	Inc	hes	DIM	Millimeters		Inches	
DIIVI	Min	Max	Min	Max	DIIVI	Min	Max	Min	Max
Α	1.35	1.75	0.053	.053 0.069 e 1.27 BSC 0.050 BSC		1.27 BSC		BSC	
A1	0.10	0.25	0.004	0.010	b	0.33	0.51	0.013	0.020
D	4.80	5.00	0.189	0.197	С	0.19	0.25	0.008	0.010
Н	5.80	6.20	0.228	0.244	θ	0°	8°	0°	8°
Е	3.80	4.00	0.150	0.157	h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050	-	-	-	-	-

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